

Vishay Siliconix

# N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0038				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0046				
Q <sub>g</sub> typ. (nC)	76				
I <sub>D</sub> (A)	120 <sup>d</sup>				
Configuration	Single				

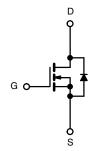
### **FEATURES**

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



### **APPLICATIONS**

- Power supply
  - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing



N-Channel MOSFET

ORDERING INFORMATION			
Package	TO-263-7L		
Lead (Pb)-free and halogen-free	SUM70040M-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	100	.,,	
Gate-source voltage	V <sub>GS</sub>	± 20	V		
Continuous dusin surrent /T 150 °C\	T <sub>C</sub> = 25 °C		120 <sup>d</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	120 <sup>d</sup>		
Pulsed drain current (t = 100 µs)	d drain current (t = 100 µs)			Α	
Avalanche current		I <sub>AS</sub>	73		
Single avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	266	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	375 b	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125 <sup>b</sup>	]	
Operating junction and storage temperature ran	nge	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) <sup>c</sup>	$R_{thJA}$	40	°C/W	
Junction-to-case (drain)	R <sub>thJC</sub>	0.4		

#### Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



www.vishay.com

# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2.5	-	4		
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C	-	-	150		
		$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_J$ = 175 °C	-	-	5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	Α	
Drain course on state resistance 3	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0030	0.0038	Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$	-	0.0035	0.0046		
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	-	82	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	5100	-	pF	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V, f = 1 MHz	-	2025	-		
Reverse transfer capacitance	$C_{rss}$		-	165	-		
Total gate charge <sup>c</sup>	$Q_g$		-	76	120	nC	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	23	-		
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	17	-		
Gate resistance	$R_g$	f = 1 MHz	0.6	3.3	6.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		-	15	30		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	22	40	20	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	55	100	ns	
Fall time <sup>c</sup>	t <sub>f</sub>		-	15	30		
Drain-Source Body Diode Ratings a	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	480	Α	
Forward voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.5	V	
Reverse recovery time	t <sub>rr</sub>		-	94	150	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	4.6	10	Α	
Reverse recovery charge	Q <sub>rr</sub>		-	0.23	0.5	μC	

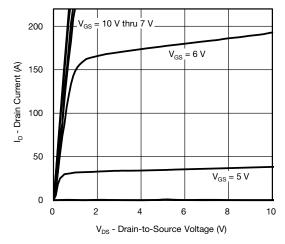
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

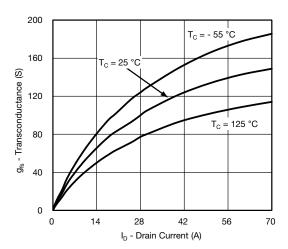
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



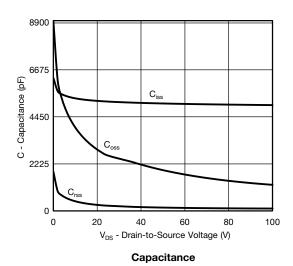
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

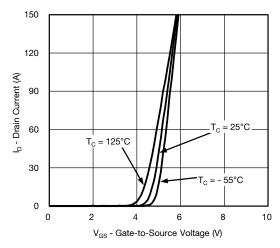


### **Output Characteristics**

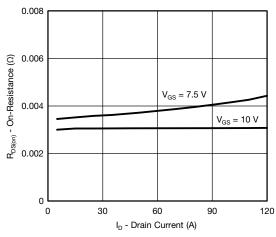


Transconductance

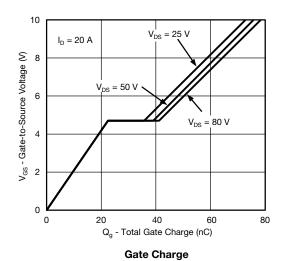




**Transfer Characteristics** 

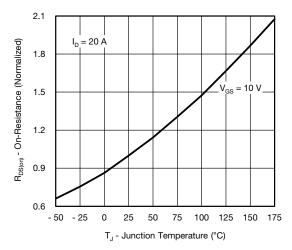


On-Resistance vs. Drain Current

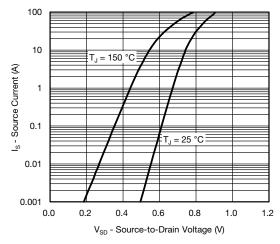




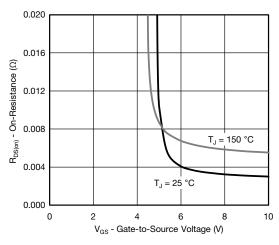
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



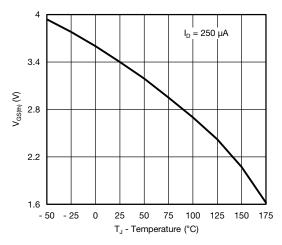
On-Resistance vs. Junction Temperature



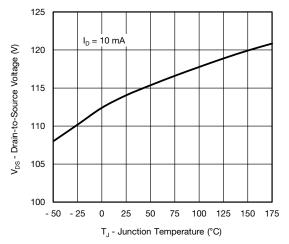
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



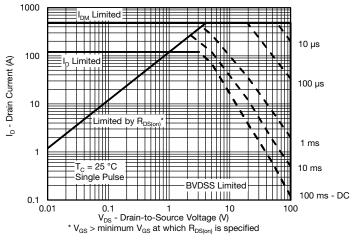
Threshold Voltage



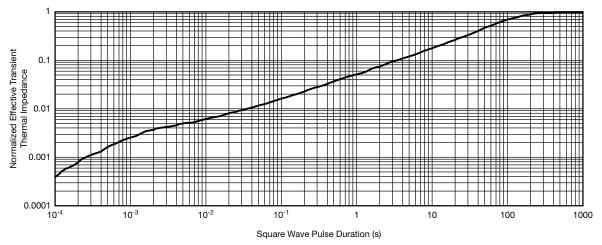
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



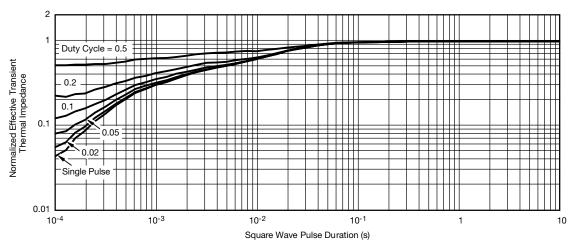
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

### Note

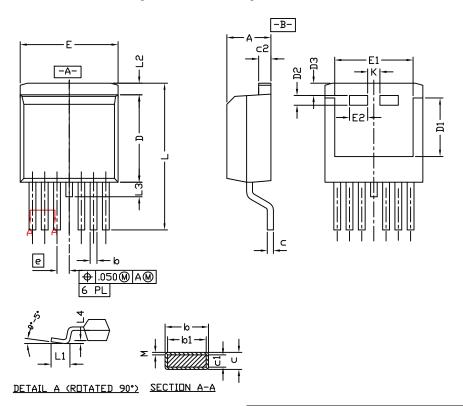
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg265814">www.vishay.com/ppg265814</a>.



# D<sup>2</sup>PAK (TO-263-7L) Case Outline



### Notes

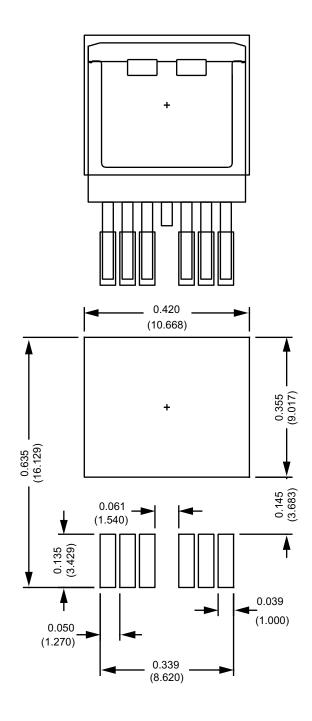
- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
Е	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050 BSC		1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010	0.010 BSC		BSC	
М	-	0.002	-	0.050	
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006					

1 Document Number: 63782



# Recommended Land Pattern D<sup>2</sup>PAK(TO-263-7L)





## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B